

General Description

The MAX4704 low-voltage, 4-channel analog multiplexer operates from a single +1.8V to +5.5V supply. The MAX4704 features break-before-make switching action with a $t_{ON} = 60$ ns and $t_{OFF} = 20$ ns at +3V.

When powered from a +2.7V supply, the device has a 60Ω (max) on-resistance (RoN), with 3Ω (max) RoN matching and 5Ω max R_{ON} flatness. The digital logic inputs are 1.8V-logic compatible from a +2.7V to +3.3V supply. The MAX4704 is available in both a space-saving 12-pin QFN (3mm x 3mm) package and a 10-pin µMAX package.

Applications

MP3 Players

Battery-Operated Equipment

Relay Replacement

Audio and Video Signal Routing

Low-Voltage Data-Acquisition Systems

Communications Circuits

PCMCIA Cards

Cellular Phones

Modems

Features

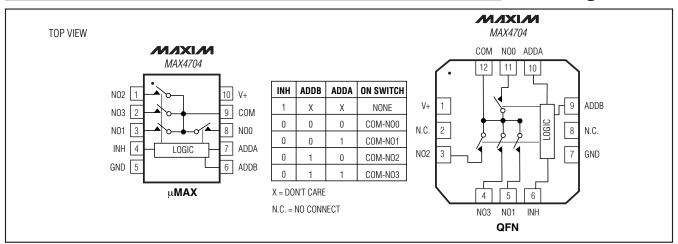
- ♦ 3mm x 3mm 12-Pin QFN Package
- ♦ Guaranteed On-Resistance: 60 Ω (max) (+2.7V Supply) 40Ω (max) (+5V Supply)
- ♦ Guaranteed Match Between Channels: 3Ω (max)
- **♦** Guaranteed Flatness Over Signal Range: 5Ω (max)
- **♦** Guaranteed Low Leakage Currents: 100pA (max) at +25°C
- ♦ Switching Time: toN = 60ns, toFF = 20ns
- ♦ +1.8V to +5.5V Single-Supply Operation
- ♦ Rail-to-Rail Signal Handling
- ♦ -3dB Bandwidth: >200MHz
- ♦ Low Crosstalk: -90dB (1MHz)
- ♦ High Off-Isolation: -85dB (1MHz)
- ♦ Low 3pC Charge Injection
- ♦ THD: 0.02%
- ♦ +1.8V CMOS-Logic Compatible

Ordering Information

PART	TEMP. RANGE	PIN-PACKAGE
MAX4704EGC	-40°C to +85°C	12 QFN-EP*
MAX4704EUB	-40°C to +85°C	10 μMAX

^{*}EP = Exposed Pad

Pin Configurations



ABSOLUTE MAXIMUM RATINGS

(Voltages Referenced to GND)	
V+	0.3V to +6V
All Other Pins (Note 1)	$-0.3V$ to $(V+ + 0.3V)$
Continuous Current COM, NO	±20mA
Peak Current COM, NO_	
(pulsed at 1ms, 10% duty cycle)	±40mA
ESD per Method 3015.7	>2kV
•	

Continuous Power Dissipation ($T_A = +70$ °C)
10-Pin µMAX (derate 4.7mW/°C above +70°C) 330mW
12-Pin QFN (derate 11.9mW/°C above +70°C) 952mW
Operating Temperature Range40°C to +85°C
Storage Temperature Range65°C to +150°C
Lead Temperature (soldering, 10s)+300°C

Note 1: Signals on INH, ADD_, NO_, and COM exceeding V+ or GND are clamped by internal diodes. Limit forward-diode current to maximum current rating.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS—Single +3V Supply

 $(V+=+2.7V \text{ to } +3.3V, V_{IH}=+1.4V, V_{IL}=+0.5V, T_A=-40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise noted.}$ Typical values are at V+=+3V and $T_A=+25^{\circ}\text{C}$.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP	MAX	UNITS
ANALOG SWITCH	•						
Analog Signal Range	V _{COM} , V _{NO} _			0		V+	V
On-Resistance	Davi	$V + = +2.7V$, $I_{COM} = 5mA$,	+25°C		50	60	
	Ron	$V_{NO_{-}} = +1.3V$	T _{MIN} to T _{MAX}			70	Ω
On-Resistance Match	ΔRON	$V+ = +2.7V$, $I_{COM} = 5mA$,	+25°C		1	3	Ω
Between Channels (Note 4)	71 IOM	$V_{NO_{-}} = +1.3V$	T _{MIN} to T _{MAX}			5	32
On-Resistance Flatness	RFLAT (ON)	$V+ = +2.7V$, $I_{COM} = 5mA$,	+25°C		3	5	Ω
(Note 5)	TIPLAT (ON)	$V_{NO} = +1V, +1.3V, +1.8V$	T _{MIN} to T _{MAX}			10	32
NO_ Off-Leakage	I _{NO_(OFF)}	$V + = +3.3V, V_{COM} = +0.3V, +3V$	+25°C	-0.1	±0.01	0.1	0.1 1 nA
Current (Note 6)	INO_(OFF)	$V_{NO_{-}} = +3V, +0.3V$	T _{MIN} to T _{MAX}	-1		1	
COM On-Leakage Current	1	$V+ = +3.3V, V_{COM} = +0.3V, +3V$ $V_{NO}_{-} = +0.3V, +3V, or floating$	+25°C	-0.5	±0.01	0.5	nA
(Note 6)	ICOM(ON)		T _{MIN} to T _{MAX}	-5		5	
COM Off-Leakage Current	1	COM(OFF) $V = +3.3V, V_{COM} = +0.3V, +3V$ $V_{NO} = +3V, +0.3V$ $T_{NO} = +0.3V$	+25°C	-0.5	±0.01	0.5	nA
(Note 6)	ICOM(OFF)		T _{MIN} to T _{MAX}	-5		5	
DYNAMIC							
Address Transition Time		$V_{NO_{-}}$ = +1.5V, R_{L} = 300 Ω , C_{L} = 35pF, Figure 2	+25°C		20	60	no
Address Transition Time	trans		T _{MIN} to T _{MAX}			70	ns
Inhibit Turn-On Time	+0.1	$V_{NO} = +1.5V, R_L = 300\Omega,$	+25°C		25	60	200
innibit rum-on nime	ton	C _L = 35pF, Figure 3	T _{MIN} to T _{MAX}			70	ns
Inhibit Turn-Off Time	torr	$V_{NO} = +1.5V, R_L = 300\Omega,$	+25°C		10	20	ns
Illinoit fulli-Oil fillie	toff	C _L = 35pF, Figure 3	T _{MIN} to T _{MAX}			30	115
Break-Before-Make Time	toou	$V_{NO} = +1.5V, R_L = 300\Omega,$	+25°C		20		ns
(Note 7)	rrini	$C_L = 35pF$, Figure 4	T _{MIN} to T _{MAX}	2			115
Charge Injection	Q	V _{GEN} = 0, R _{GEN} = 0, C _L = 1.0nF, Figure 5			2		рС

ELECTRICAL CHARACTERISTICS—Single +3V Supply (continued)

 $(V+=+2.7V \text{ to } +3.3V, V_{IH}=+1.4V, V_{IL}=+0.5V, T_A=-40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise noted.}$ Typical values are at V+=+3V and $T_A=+25^{\circ}\text{C}.)$ (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP	MAX	UNITS
On-Channel -3dB Bandwidth	BW	Signal = 0dBm, 50Ω in and out, Figure 6			>200		MHz
Off-Isolation (Note 8)	V _{ISO}	$f = 1MHz$, $R_L = 50\Omega$, $C_L = 5pF$, Figure 6			-85		dB
Crosstalk (Note 9)	VCT	$f = 1MHz$, $R_L = 50\Omega$, $C_L = 5pF$, Figure 6			-90		dB
NO_ Off-Capacitance	C _{NO_(OFF)}	f = 1MHz, V _{NO} = GND, Figure 7			7		рF
COM On-Capacitance	C _{COM} (ON)	f = 1MHz, V _{NO} = GND, Figure 7			19		pF
COM Off-Capacitance	CCOM(OFF)	f = 1MHz, V _{NO} = GND, Figure 7			15		рF
DIGITAL I/O							
Input Logic High	VIH			1.4			V
Input Logic Low	VIL					0.5	V
Input Leakage Current	I _{IH} , I _{IL}	ADD_, INH = 0 or V+		-1		1	μΑ
SUPPLY							
Power-Supply Range	V+			1.8		5.5	V
Power-Supply Current	l+	V+ = +5.5V, ADD_, INH = 0 or V+				1	μΑ

ELECTRICAL CHARACTERISTICS—Single +5V Supply

 $(V+=+4.5V \text{ to } +5.5V, V_{IH}=+2.0V, V_{IL}=+0.8V, T_A=-40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise noted.}$ Typical values are at V+=+5V and $T_A=+25^{\circ}\text{C}.)$ (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP	MAX	UNITS
ANALOG SWITCH							
Analog Signal Range	V _{COM} , V _{NO} _			0		V+	V
On Registance	Davi	$V + = +4.5V$, $I_{COM} = 5mA$,	+25°C		30	40	Ω
On-Resistance	Ron	$V_{NO} = +3.5V$	T _{MIN} to T _{MAX}			50	
On-Resistance Match	A.D.a.i	ΔR_{ON} $V_{+} = +4.5V, I_{COM} = 5mA, V_{NO} = +3.5V$	+25°C		1	2	Ω
Between Channels (Note 4)	ΔηΟΝ		T _{MIN} to T _{MAX}			3	
On-Resistance Flatness	De. 17 (01)	$V+ = +4.5V$, $I_{COM} = 5mA$,	+25°C		3	5	Ω
(Note 5)	MFLAT (ON)	RFLAT (ON) $V_{NO} = +1V, +2.25V, +3.5V$	T _{MIN} to T _{MAX}			10	22
NO_ Off-Leakage	huo (055)	$V + = +5.5V, V_{COM} = +0.5V, +5V$	+25°C	-0.1	±0.01	0.1	
Current (Note 6)	INO_(OFF)	$V_{NO} = +5V, +0.5V$	T _{MIN} to T _{MAX}	-1		1	nA
COM On-Leakage Current	lo ou woun	$V + = +5.5V, V_{COM} = +0.5V, +5V$	+25°C	-0.5	±0.01	0.5	nA
(Note 6)	ICOM(ON)	V_{NO} = +0.5V, +5V, or floating	T _{MIN} to T _{MAX}	-5		5	11A

ELECTRICAL CHARACTERISTICS—Single +5V Supply (continued)

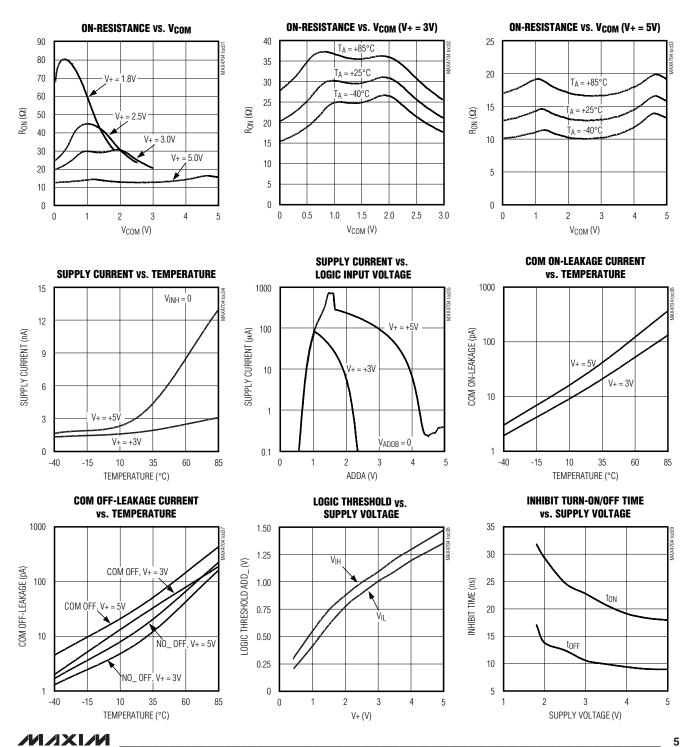
 $(V+=+4.5V \text{ to } +5.5V, V_{IH}=+2.0V, V_{IL}=+0.8V, T_A=-40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise noted.}$ Typical values are at V+=+5V and $T_A=+25^{\circ}\text{C}.)$ (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP	MAX	UNITS
COM Off-Leakage Current	loov voee	V+ = +5.5V, V _{COM} = +0.5V, +5V V _{NO} = +5V, +0.5V	+25°C	-0.5	±0.01	0.5	nA
CON On-Leakage Current	ICOM(OFF)		T _{MIN} to T _{MAX}	-5		5	IIA
DYNAMIC							
Address Transition Time	t _{TRANS}	$V_{NO} = +3V, R_L = 300\Omega,$	+25°C		15	35	ns
Address Hanshoff Fifte	THAINS	C _L = 35pF, Figure 2	T _{MIN} to T _{MAX}			40	110
Inhibit Turn-On Time	ton	$V_{NO} = +3V, R_L = 300\Omega,$	+25°C		18	35	ns
minibit rum-on time	TON	C _L = 35pF, Figure 3	T _{MIN} to T _{MAX}			40	110
Inhibit Turn-Off Time	toff	$V_{NO} = +3V, R_L = 300\Omega,$	+25°C		9	20	ns
	OFF	C _L = 35pF, Figure 3	T _{MIN} to T _{MAX}			30	30
Break-Before-Make Time	tbbm	$V_{NO} = +3V, R_L = 300\Omega,$	+25°C		20		ns
(Note 7)	rddivi	C _L = 35pF, Figure 4	T _{MIN} to T _{MAX}	2			110
Charge Injection	Q	$V_{GEN} = 0$, $R_{GEN} = 0$, $C_L = 1.0$ nF, Figure 5			3		рС
On-Channel -3dB Bandwidth	BW	Signal = 0dBm, 50Ω in and out, Figure 6			>200		MHz
Off-Isolation (Note 8)	V _{ISO}	$f = 1MHz$, $R_L = 50\Omega$, $C_L = 5pF$, Figure 6			-85		dB
Crosstalk (Note 9)	VCT	$f = 1MHz$, $R_L = 50\Omega$, $C_L = 5pF$, Figure 6			-90		dB
Total Harmonic Distortion	THD	$f = 20$ Hz to 20 kHz, 1 Vp-p, $R_L = 600\Omega$			0.02		%
DIGITAL I/O							
Input Logic High	VIH			2.0			V
Input Logic Low	V _{IL}					8.0	V
Input Leakage Current	I _{IH} , I _{IL}	ADD_, INH = 0 or V+		-1		1	μΑ
SUPPLY							
Power-Supply Range	V+			1.8		5.5	V
Positive Supply Current	l+	V+ = +5.5V, ADD_, INH = 0 or V+				1	μΑ

- **Note 2:** The algebraic convention, where the most negative value is a minimum and the most positive value a maximum, is used in this data sheet.
- **Note 3:** -40°C specifications are guaranteed by design.
- **Note 4:** $\Delta R_{ON} = R_{ON(MAX)} R_{ON(MIN)}$.
- **Note 5:** Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges.
- **Note 6:** Leakage currents are 100% tested at $T_A = +85$ °C. Limits across the full temperature range are guaranteed by correlation.
- Note 7: Guaranteed by design.
- Note 8: Off-Isolation = $20log_{10}$ (V_{COM} / V_{NO}), V_{COM} = output, V_{NO} = input to off switch.
- Note 9: Between any two switches.

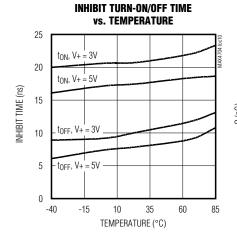
Typical Operating Characteristics

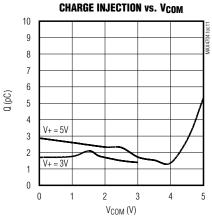
 $(T_A = +25^{\circ}C, \text{ unless otherwise noted.})$

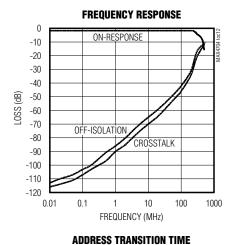


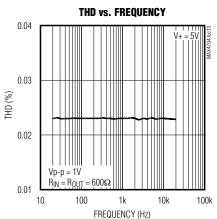
Typical Operating Characteristics (continued)

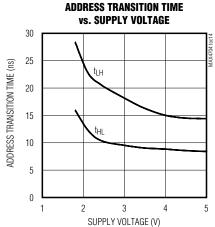
 $(T_A = +25^{\circ}C, \text{ unless otherwise noted.})$

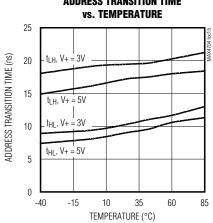












Pin Description

Р	PIN μΜΑΧ QFN-EP		PIN		FUNCTION		
μMAX			FUNCTION				
10	1	V+	Positive Supply Voltage				
_	2, 8	N.C.	No Connection. Not internally connected.				
1	3	NO2	Analog Switch 2. Normally open.				
2	4	NO3	Analog Switch 3. Normally open.				
3	5	NO1	Analog Switch 1. Normally open.				
4	6	INH	Inhibit. Connect to GND for normal operation. Connect to logic-level high to turn all switches off.				
5	7	GND	Ground				
6	9	ADDB	Address Decoder Selection B				
7	10	ADDA	Address Decoder Selection A				
8	11	NO0	Analog Switch 0. Normally open.				
9	12	COM	Analog Switch Common Terminal				
_	_	EP	Exposed Pad. Internally connected to GND. Connect to a large ground plane to maximize thermal performance; not intended as an electrical connection point (QFN package only).				

Detailed Description

The MAX4704 low-voltage, 4-channel analog multiplexer operates from a single +1.8V to +5.5V supply. When powered from a +2.7V supply, the device has a 60Ω (max) on-resistance (RoN), with 3Ω (max) RoN matching and 5Ω (max) RoN flatness. The digital logic inputs are +1.8V-logic compatible from a +2.7V to +3.3V supply.

Applications Information

Digital Control Inputs

The MAX4704 logic inputs are +1.8V CMOS logic compatible for 3V operation and TTL compatible for 5V operation of V+. Driving ADD_ rail-to-rail minimizes power consumption.

Analog Signal Levels

Analog signals that range over the entire supply voltage (V+ to GND) are passed with very little change in on-resistance (see *Typical Operating Characteristics*). The switches are bidirectional, so the NO_ and COM pins can be either inputs or outputs.

Power-Supply Sequencing and Overvoltage Protection

Caution: Do not exceed the absolute maximum ratings because stresses beyond those listed may cause permanent damage to devices.

Proper power-supply sequencing is recommended for all CMOS devices. Always apply V+ before applying analog signals, especially if the analog signal is not current limited. If this sequencing is not possible, and if the analog inputs are not current limited to <20mA, add a small-signal diode

(D1) as shown in Figure 1. If the analog signal can dip below GND, add D2. Adding protection diodes reduces the analog range to a diode drop (about 0.7V) below V+ (for D1), and a diode drop above ground (for D2). On-resistance increases slightly at low supply voltages. Maximum supply voltage (V+) must not exceed +6V.

Adding protection diode D2 causes the logic threshold to be shifted relative to GND. TTL compatibility is not guaranteed when D2 is added.

Protection diodes D1 and D2 also protect against some overvoltage situations. In the circuit in Figure 1, if the supply voltage is below the absolute maximum rating, and if a fault voltage up to the absolute maximum rating is applied to an analog signal pin, no damage will result.

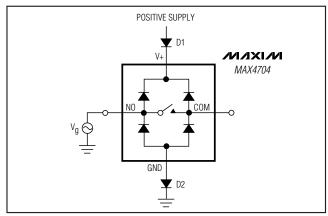


Figure 1. Overvoltage Protection Using Two External Blocking Diodes

Test Circuits/Timing Diagrams

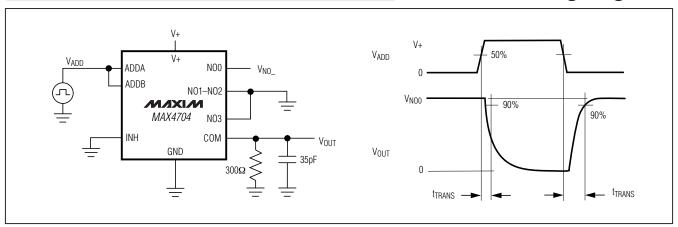


Figure 2. Address Transition Time

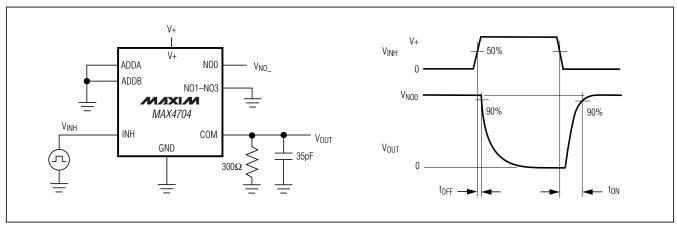


Figure 3. Inhibit Switching Times

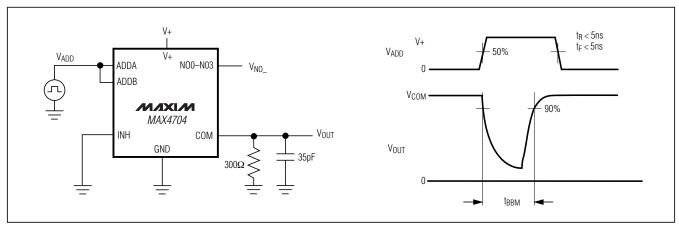


Figure 4. Break-Before-Make Interval

Test Circuits/Timing Diagrams (continued)

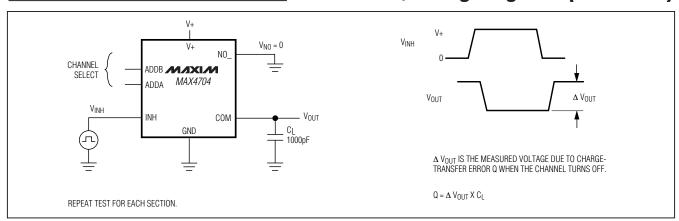


Figure 5. Charge Injection

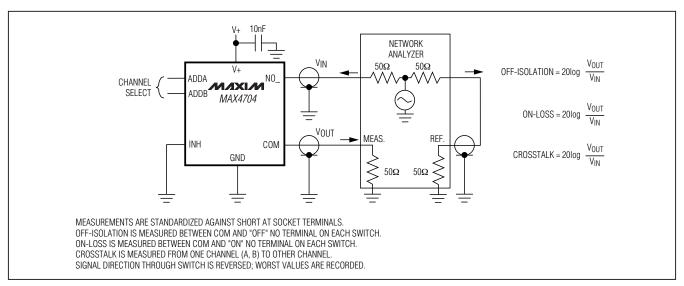


Figure 6. Off-Isolation, On-Loss, and Crosstalk

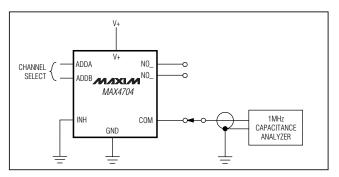


Figure 7. NO_/COM Capacitance

Chip Information

TRANSISTOR COUNT: 256

PROCESS: CMOS

Package Information

For the latest package outline information and land patterns, go to www.maxim-ic.com/packages.

PACKAGE TYPE	PACKAGE CODE	DOCUMENT NO.
12 QFN-EP	G1233-1	<u>21-0102</u>
10 μMAX	_	<u>21-0061</u>

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	10/01	Initial release	_
1	10/08	Inserted exposed paddle description	1, 7

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